

Gari Harris

List of Publications by Year in descending order

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Version: 2024-02-01

8
papers

103
citations

2257833

3
h-index

2053595

5
g-index

8
all docs

8
docs citations

8
times ranked

60
citing authors

#	ARTICLE	IF	CITATIONS
1	Low thermal budget in situ removal of oxygen and carbon on silicon for silicon epitaxy in an ultrahigh vacuum rapid thermal chemical vapor deposition reactor. Applied Physics Letters, 1995, 66, 1255-1257.	1.5	16
2	Ultrahigh Vacuum Rapid Thermal Chemical Vapor Deposition of Epitaxial Silicon on (100) Silicon: II . Carbon Incorporation into Layers and at Interfaces of Multilayer Structures. Journal of the Electrochemical Society, 1995, 142, 3970-3974.	1.3	1
3	Growth Kinetics, Silicon Nucleation on Silicon Dioxide, and Selective Epitaxy Using Disilane and Hydrogen in an Ultrahigh Vacuum Rapid Thermal Chemical Vapor Deposition Reactor. Journal of the Electrochemical Society, 1994, 141, 3269-3273.	1.3	35
4	Nucleation and Growth of Polycrystalline Silicon Films in an Ultra high Vacuum Rapid Thermal Chemical Vapor Deposition Reactor Using Disilane and Hydrogen. Materials Research Society Symposia Proceedings, 1994, 343, 673.	0.1	0
5	Phase transitions during solid-state formation of cobalt germanide by rapid thermal annealing. Journal of Applied Physics, 1993, 74, 4455-4460.	1.1	49
6	Self-Aligned Formation of C54 Titanium Germanosilicide Using Rapid Thermal Processing and Application to Raised, Ultrashallow Junctions. Materials Research Society Symposia Proceedings, 1993, 320, 311.	0.1	2
7	Cleaning during Initial Stages of Epitaxial Growth in an Ultrahigh Vacuum Rapid Thermal Chemical Vapor Deposition Reactor. Materials Research Society Symposia Proceedings, 1993, 334, 463.	0.1	0
8	Silicon Nucleation on Silicon Dioxide and Selective Epitaxy In An Ultra-High Vacuum Rapid Thermal Chemical Vapor Deposition Reactor Using Disilane In Hydrogen. Materials Research Society Symposia Proceedings, 1993, 334, 519.	0.1	0